

# Kelson D Chabak

## List of Publications by Year in descending order

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28  
papers

2,823  
citations

304743

22  
h-index

580821

25  
g-index

28  
all docs

28  
docs citations

28  
times ranked

1646  
citing authors

#	ARTICLE	IF	CITATIONS
1	Thermally-Aware Layout Design of $\text{In}^{2+}$ -Ga <sub>2</sub> O <sub>3</sub> Lateral MOSFETs. IEEE Transactions on Electron Devices, 2022, 69, 1251-1257.	3.0	11
2	$\text{In}^{2+}$ -Gallium oxide power electronics. APL Materials, 2022, 10, .	5.1	184
3	Scaled T-Gate $\text{In}^{2+}$ -Ga <sub>2</sub> O <sub>3</sub> MESFETs With 2.45 kV Breakdown and High Switching Figure of Merit. IEEE Electron Device Letters, 2022, 43, 1307-1310.	3.9	8
4	Electrical and chemical analysis of Ti/Au contacts to $\text{In}^{2+}$ -Ga <sub>2</sub> O <sub>3</sub> . APL Materials, 2021, 9, 061104.	5.1	23
5	Towards the Integration of Hf <sub>0.8</sub> Zr <sub>0.2</sub> O <sub>2</sub> -based Negative Capacitance Dielectrics on $\text{In}^{2+}$ -Ga <sub>2</sub> O <sub>3</sub> Substrates. , 2021, , .		1
6	Lateral $\text{In}^{2+}$ -Ga <sub>2</sub> O <sub>3</sub> field effect transistors. Semiconductor Science and Technology, 2020, 35, 013002.	2.0	85
7	Self-Heating Characterization of $\text{In}^{2+}$ -Ga <sub>2</sub> O <sub>3</sub> Thin-Channel MOSFETs by Pulsed $\text{I}^2$ and Raman Nanothermography. IEEE Transactions on Electron Devices, 2020, 67, 204-211.	3.0	18
8	Toward high voltage radio frequency devices in $\text{In}^{2+}$ -Ga <sub>2</sub> O <sub>3</sub> . Applied Physics Letters, 2020, 117, .	3.3	23
9	Pulsed Power Performance of $\text{In}^{2+}$ -Ga <sub>2</sub> O <sub>3</sub> MOSFETs at L-Band. IEEE Electron Device Letters, 2020, 41, 989-992.	3.9	32
10	RF Power Performance of Sc(Al,Ga)N/GaN HEMTs at Ka-Band. IEEE Electron Device Letters, 2020, 41, 1181-1184.	3.9	41
11	Field-Effect Transistors 1. Springer Series in Materials Science, 2020, , 563-582.	0.6	0
12	Thin channel $\text{In}^{2+}$ -Ga <sub>2</sub> O <sub>3</sub> MOSFETs with self-aligned refractory metal gates. Applied Physics Express, 2019, 12, 126501.	2.4	35
13	High Aspect Ratio $\text{In}^{2+}$ -Ga <sub>2</sub> O <sub>3</sub> Fin Arrays with Low-Interface Charge Density by Inverse Metal-Assisted Chemical Etching. ACS Nano, 2019, 13, 8784-8792.	14.6	57
14	ScAlN/GaN High-Electron-Mobility Transistors With 2.4-A/mm Current Density and 0.67-S/mm Transconductance. IEEE Electron Device Letters, 2019, 40, 1056-1059.	3.9	63
15	Demonstration of high mobility and quantum transport in modulation-doped $\text{In}^{2+}$ -(Al <sub>x</sub> Ga <sub>1-x</sub> ) <sub>2</sub> O <sub>3</sub> /Ga <sub>2</sub> O <sub>3</sub> heterostructures. Applied Physics Letters, 2018, 112, .	3.3	264
16	Recessed-Gate Enhancement-Mode $\text{In}^{2+}$ -Ga <sub>2</sub> O <sub>3</sub> MOSFETs. IEEE Electron Device Letters, 2018, 39, 67-70.	3.9	187
17	Si content variation and influence of deposition atmosphere in homoepitaxial Si-doped $\text{In}^{2+}$ -Ga <sub>2</sub> O <sub>3</sub> films by pulsed laser deposition. APL Materials, 2018, 6, 101102.	5.1	40
18	Donors and deep acceptors in $\text{In}^{2+}$ -Ga <sub>2</sub> O <sub>3</sub> . Applied Physics Letters, 2018, 113, .	3.3	203

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19	$\eta$ -Ga <sub>2</sub> O <sub>3</sub> MOSFETs for Radio Frequency Operation. IEEE Electron Device Letters, 2017, 38, 790-793.	3.9	248
20	Ge-Doped $\eta$ -Ga <sub>2</sub> O <sub>3</sub> MOSFETs. IEEE Electron Device Letters, 2017, 38, 775-778.	3.9	165
21	High pulsed current density $\hat{\Gamma}^2$ -Ga <sub>2</sub> O <sub>3</sub> MOSFETs verified by an analytical model corrected for interface charge. Applied Physics Letters, 2017, 110, .	3.3	75
22	Incomplete Ionization of a 110 $\hat{\epsilon}$ meV Unintentional Donor in $\hat{\Gamma}^2$ -Ga <sub>2</sub> O <sub>3</sub> and its Effect on Power Devices. Scientific Reports, 2017, 7, 13218.	3.3	84
23	Gate-recessed, laterally-scaled $\hat{\Gamma}^2$ -Ga <sub>2</sub> O <sub>3</sub> MOSFETs with high-voltage enhancement-mode operation. , 2017, , .		7
24	Highly conductive homoepitaxial Si-doped Ga <sub>2</sub> O <sub>3</sub> films on (010) $\hat{\Gamma}^2$ -Ga <sub>2</sub> O <sub>3</sub> by pulsed laser deposition. Applied Physics Letters, 2017, 111, .	3.3	128
25	Enhancement-mode Ga <sub>2</sub> O <sub>3</sub> wrap-gate fin field-effect transistors on native (100) $\hat{\Gamma}^2$ -Ga <sub>2</sub> O <sub>3</sub> substrate with high breakdown voltage. Applied Physics Letters, 2016, 109, .	3.3	298
26	3.8-MV/cm Breakdown Strength of MOVPE-Grown Sn-Doped $\eta$ -Ga <sub>2</sub> O <sub>3</sub> MOSFETs. IEEE Electron Device Letters, 2016, 37, 902-905.	3.9	468
27	Implementation of High-Power-Density $\eta$ -Band AlGa <sub>2</sub> N/GaN High Electron Mobility Transistors in a Millimeter-Wave Monolithic Microwave Integrated Circuit Process. IEEE Electron Device Letters, 2015, 36, 1004-1007.	3.9	50
28	Strained AlInN/GaN HEMTs on SiC With 2.1-A/mm Output Current and 104-GHz Cutoff Frequency. IEEE Electron Device Letters, 2010, 31, 561-563.	3.9	25